

62mm C-Serien Modul mit Trench/Feldstop IGBT³ und Emitter Controlled³Diode
62mm C-series module with trench/fieldstop IGBT³ and Emitter Controlled³ diode

初步数据
Preliminary Data

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
连续集电极直流电流 Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj\text{max}} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 150^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	200 310	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ms}$	I_{CRM}	400	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 150$	P_{tot}	1250	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 200\text{A}, V_{GE} = 15\text{V}$ $I_C = 200\text{A}, V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{sat}}$	2,00 2,40	2,45	V V
栅极阈值电压 Gate threshold voltage	$I_C = 8,00\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	5,2	5,8	6,4 V
栅极电荷 Gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$		Q_G	2,30		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	3,8		Ω
输入电容 Input capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{ies}	18,0		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		C_{res}	0,60		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		3,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 200\text{A}, V_{CE} = 900\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{on}} = 6,8\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{on}}$	0,28 0,30		μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 200\text{A}, V_{CE} = 900\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{on}} = 6,8\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_r	0,08 0,10		μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 200\text{A}, V_{CE} = 900\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{off}} = 6,8\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{off}}$	0,80 1,00		μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 200\text{A}, V_{CE} = 900\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{off}} = 6,8\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	t_f	0,12 0,20		μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 200\text{A}, V_{CE} = 900\text{V}, L_S = 60\text{nH}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{on}} = 6,8\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{on}	58,0 78,0		mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 200\text{A}, V_{CE} = 900\text{V}, L_S = 60\text{nH}$ $V_{GE} = \pm 15\text{V}$ $R_{G\text{off}} = 6,8\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{off}	43,0 63,0		mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{V}, V_{CC} = 1000\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		I_{SC}	800		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		0,10	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,033		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	125	$^{\circ}\text{C}$

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初步数据
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二极管, 逆变器 / Diode, Inverter
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1700	V
连续正向直流电流 Continuous DC forward current		I_F	200	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	400	A
I^2t -值 I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	6600	A^2s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 200\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 200\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	V_F	1,80 1,90	2,20	V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 200\text{ A}, -di_F/dt = 2700\text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	I_{RM}	210 230		A A
恢复电荷 Recovered charge	$I_F = 200\text{ A}, -di_F/dt = 2700\text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	Q_r	51,0 85,0		μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 200\text{ A}, -di_F/dt = 2700\text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 900\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	E_{rec}	25,0 48,0		mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,16	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,052		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	125	$^{\circ}\text{C}$

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模块 / Module

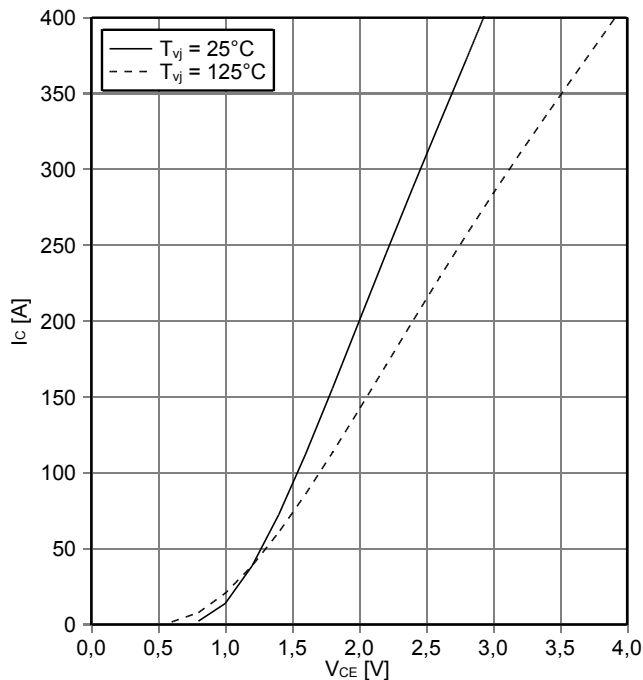
绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	3,4		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		29,0 23,0		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		23,0 11,0		mm
相对电痕指数 Comperative tracking index		CTI	> 400		
			min.	typ.	max.
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个模块 / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R _{thCH}		0,01	K/W
杂散电感, 模块 Stray inductance module		L _{sCE}		20	nH
模块引线电阻, 端子- 芯片 Module lead resistance, terminals - chip	T _C = 25°C, 每个开关 / per switch	R _{CC+EE'}		0,60	mΩ
储存温度 Storage temperature		T _{stg}	-40		125 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,00	-	6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	2,5	-	5,0 Nm
重量 Weight		G		340	g

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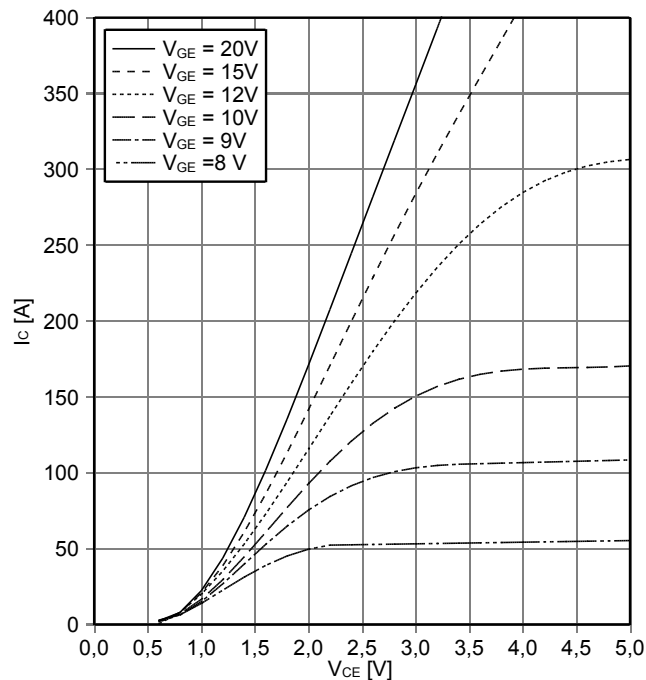
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



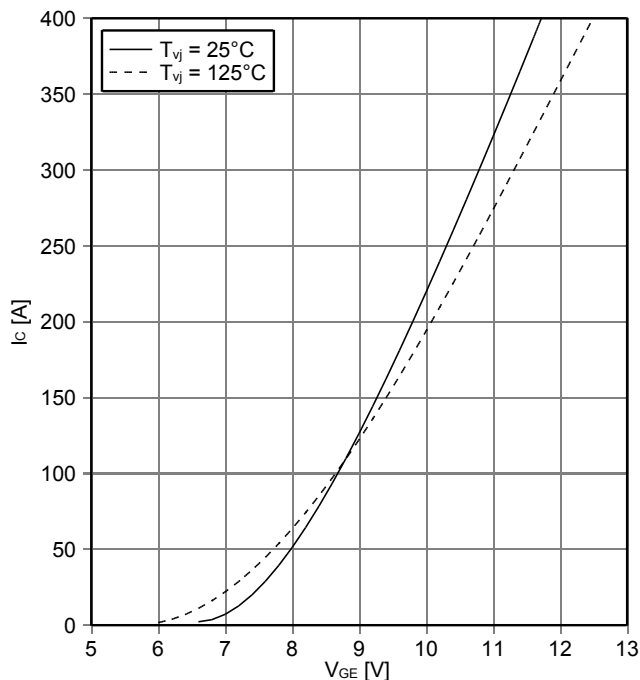
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



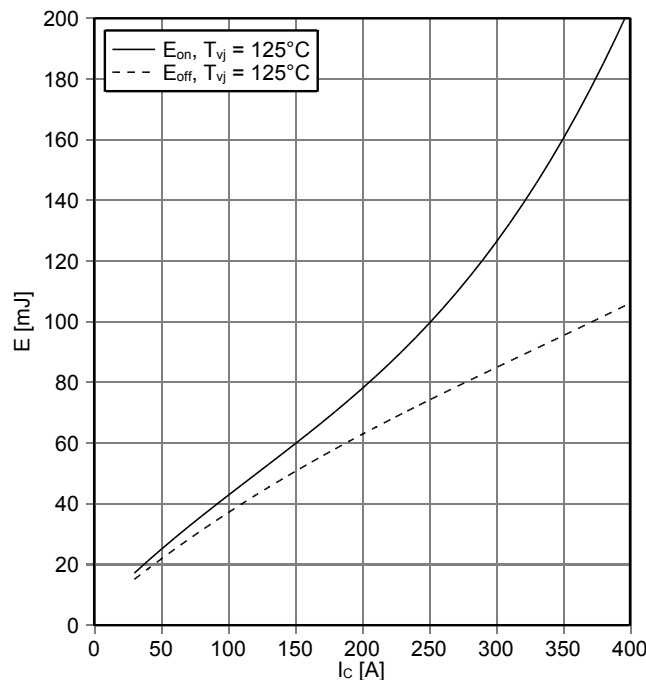
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 6.8\ \Omega, R_{Goff} = 6.8\ \Omega, V_{CE} = 900\text{ V}$

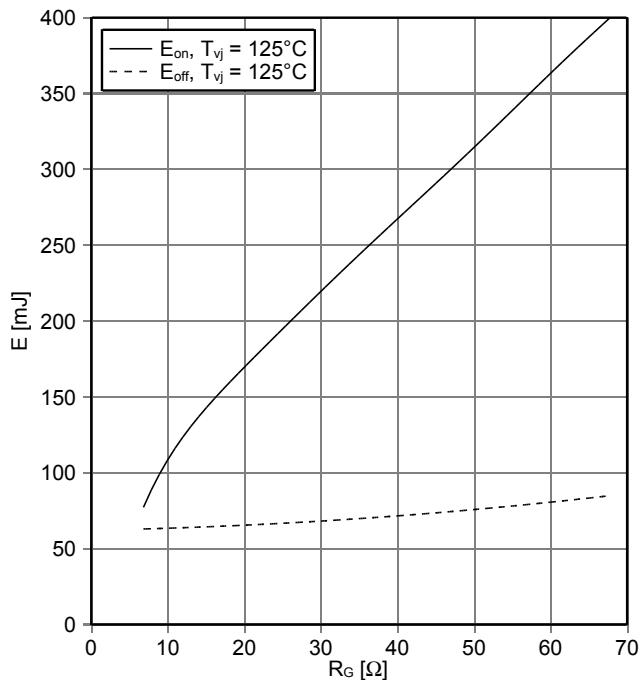


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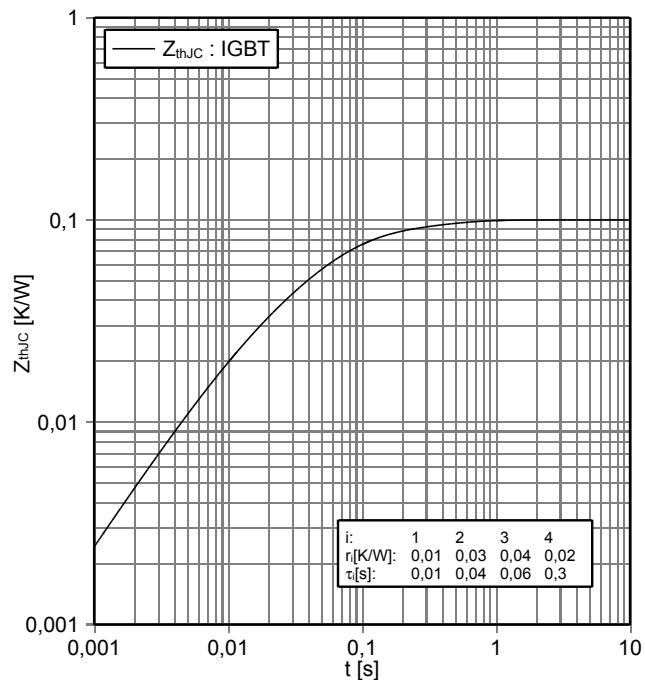
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 200\text{ A}, V_{CE} = 900\text{ V}$



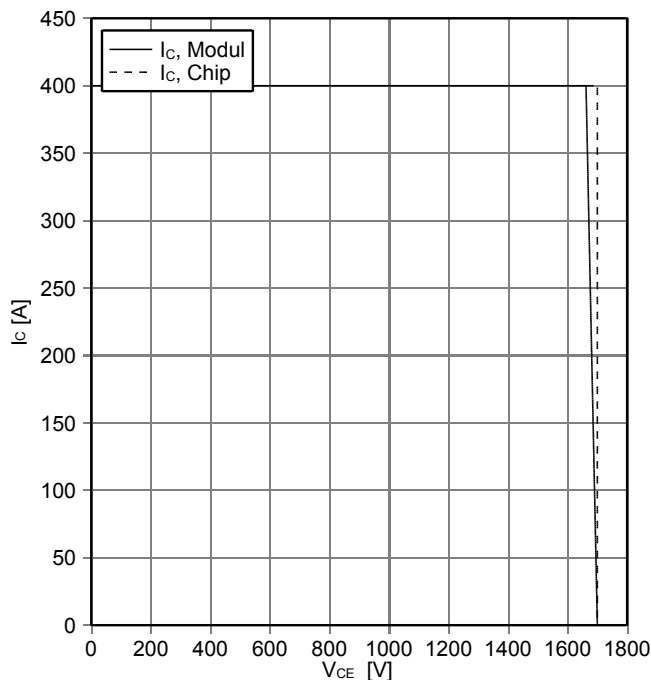
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



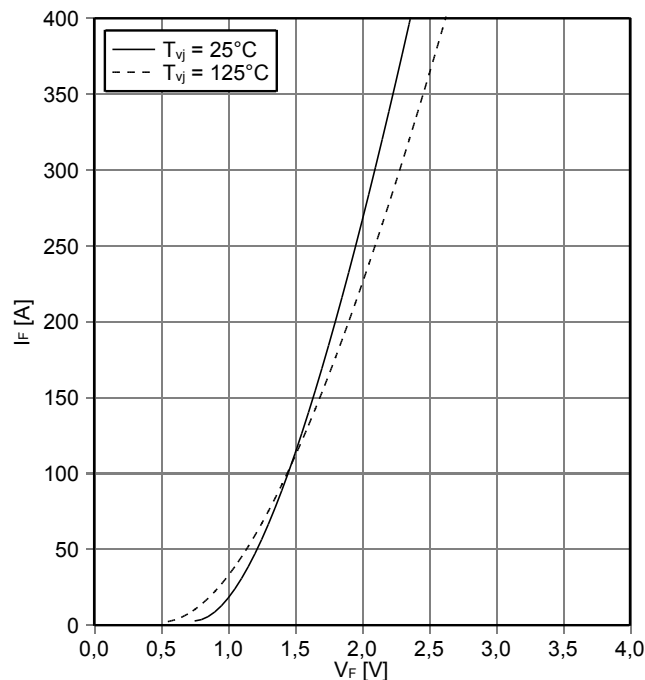
反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 6.8\ \Omega, T_{vj} = 125^\circ\text{C}$



正向偏压特性 二极管, 逆变器 (典型)
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



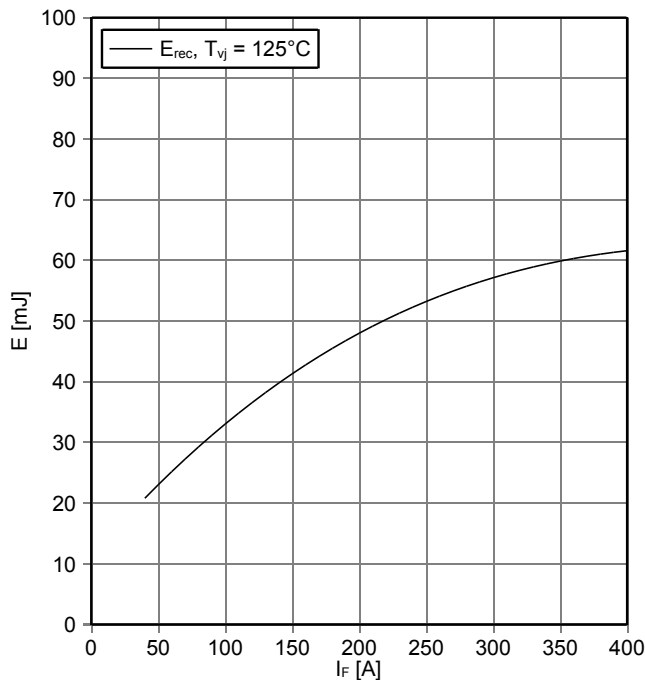
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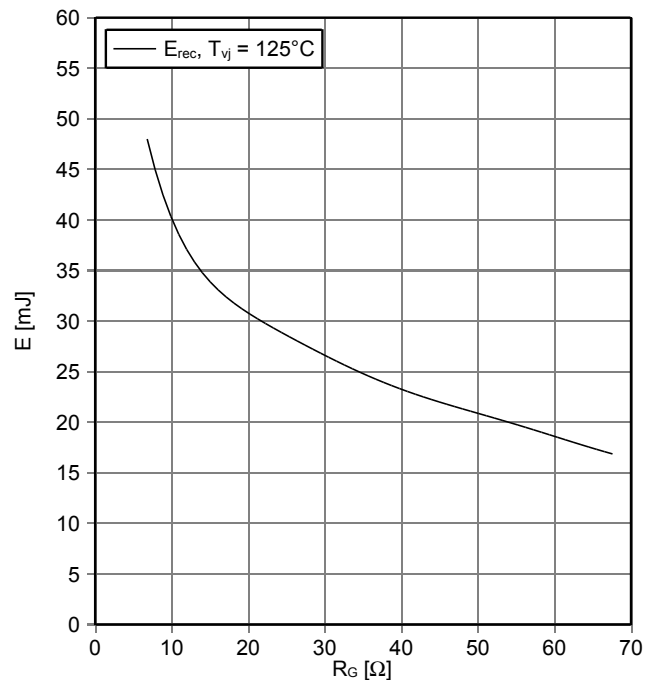
开关损耗 二极管, 逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 6.8 \Omega, V_{CE} = 900 V$



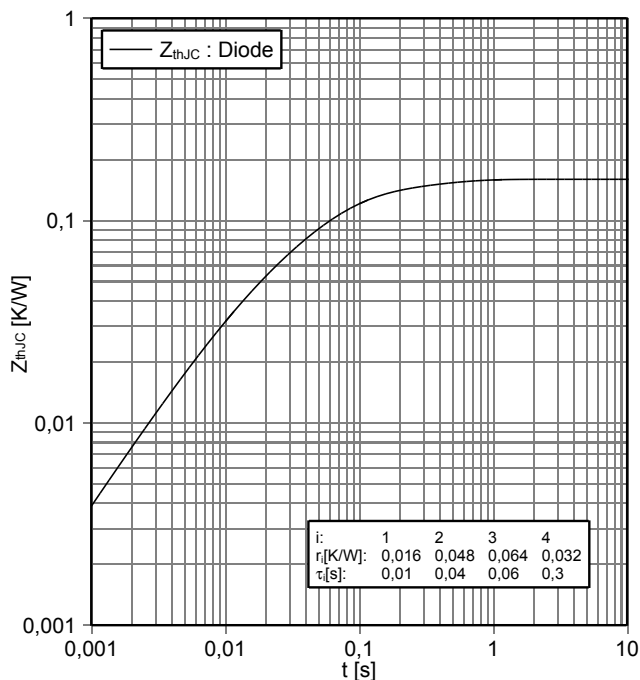
开关损耗 二极管, 逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 200 A, V_{CE} = 900 V$



瞬态热阻抗 二极管, 逆变器
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$

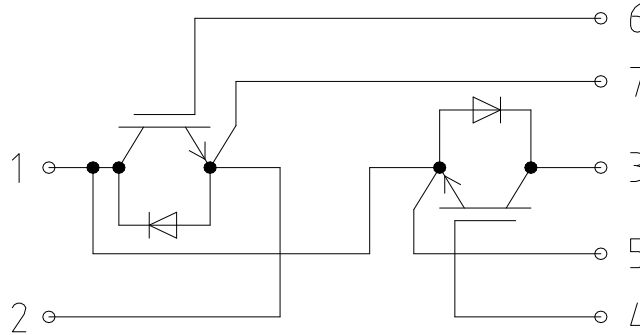


i:	1	2	3	4
ri[K/W]:	0,016	0,048	0,064	0,032
τi[s]:	0,01	0,04	0,06	0,3

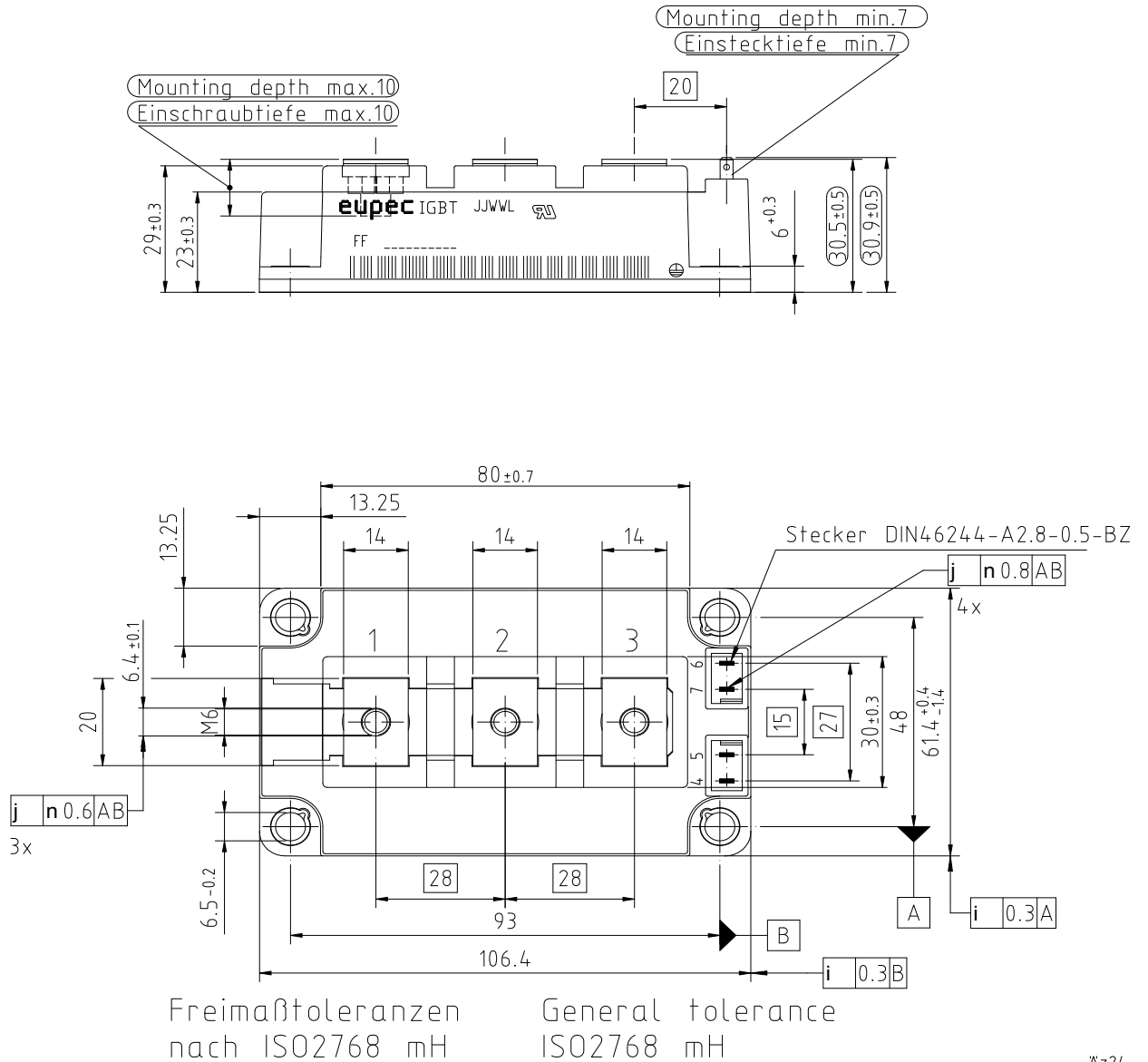
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接线图 / circuit_diagram_headline



封装尺寸 / package outlines



Az24

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**初步数据
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使用条件和条款

使用条件和条款

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- the conclusion of Quality Agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery depended on the realization of any such measures.

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